NIPPON PRECISION CIRCUITS INC.

CF5014 series

Crystal Oscillator Module ICs

OVERVIEW

The CF5014 series are fundamental frequency crystal oscillator ICs. They are available for frequencies up to 60MHz. The chip layout is optimized, resulting in a large reduction in chip size, when compared to existing devices.

FEATURES

- 2.7 to 5.5V operating supply voltage range
- Up to 60MHz oscillation frequency range
- – 40 to 85°C operating temperature range
- Oscillation capacitors built-in
  - C_G = 18pF, C_D = 18pF
- Inverter amplifier feedback resistor built-in
- Standby function
  - High impedance in standby mode, oscillator stops
- Low standby current
  - Power-save pull-up resistor built-in
- f_O, $f_O/2$, $f_O/4$, $f_O/8$, or $f_O/16$ output frequency, determined by internal connection
- CMOS output duty level (1/2VDD)
- Molybdenum-gate CMOS process
- Chip form (CF5014AL×)

SERIES CONFIGURATION

Version	Recommended operating frequency range[1] [MHz]			Built-in capacitance [pF]		Output frequency	Standby function
	V_{DD} = 2.7 to 3.6V		V_{DD} = 4.5 to 5.5V				
	C_L = 15pF	C_L = 30pF	C_L = 30pF	C_G	C_D		
CF5014AL1	4 to 60	4 to 40	4 to 60	18	18	f_O	Yes
CF5014AL2						$f_O/2$	Yes
CF5014AL3						$f_O/4$	Yes
CF5014AL4						$f_O/8$	Yes
CF5014AL5						$f_O/16$	Yes

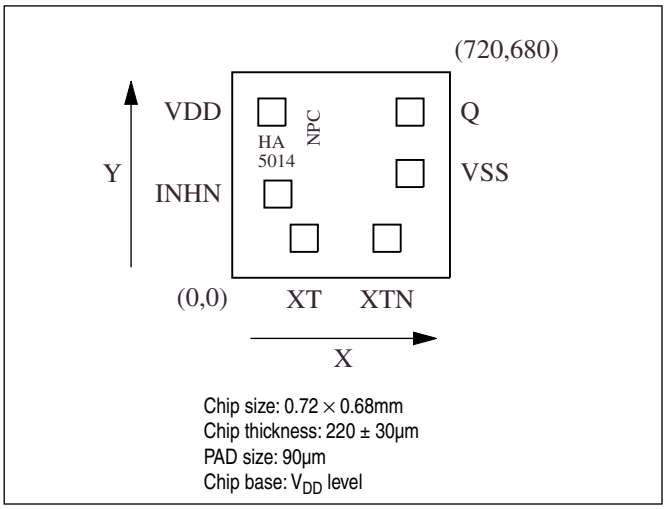
1. The recommended operating frequency is a yardstick value derived from the crystal used for NPC characteristics authentication. However, the oscillator frequency band is not guaranteed. Specifically, the characteristics can vary greatly due to crystal characteristics and mounting conditions, so the oscillation characteristics of components must be carefully evaluated.

ORDERING INFORMATION

Device	Package
CF5014AL×–2	Chip form

PAD LAYOUT

(Unit: µm)

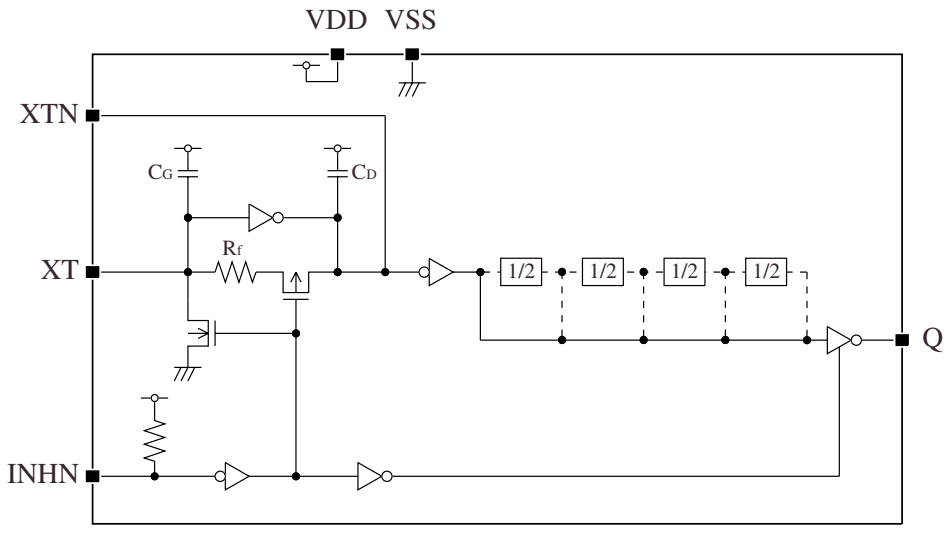


Chip size: 0.72 × 0.68mm
Chip thickness: 220 ± 30µm
PAD size: 90µm
Chip base: V_{DD} level

PIN DESCRIPTION and PAD DIMENSIONS

Name	I/O	Description		Pad dimensions [µm]	
				X	Y
INHN	I	Output state control input. High impedance when LOW (oscillator stops). Power-saving pull-up resistor built-in.		151	277
XT	I	Amplifier input	Crystal connection pins. Crystal is connected between XT and XTN.	238	131
XTN	O	Amplifier output		512	131
VSS	–	Ground		588	345
Q	O	Output. Output frequency (f_O, $f_O/2$, $f_O/4$, $f_O/8$, $f_O/16$) determined by internal connection		588	548
VDD	–	Supply voltage		131	548

BLOCK DIAGRAM



INHN = LOW active

SPECIFICATIONS

Absolute Maximum Ratings

V_{SS} = 0V

Parameter	Symbol	Condition	Rating	Unit
Supply voltage range	V_{DD}		–0.5 to +7.0	V
Input voltage range	V_{IN}		–0.5 to V_{DD} + 0.5	V
Output voltage range	V_{OUT}		–0.5 to V_{DD} + 0.5	V
Operating temperature range	T_{opr}		–40 to +85	°C
Storage temperature range	T_{STG}		–65 to +150	°C
Output current	I_{OUT}		12	mA

Recommended Operating Conditions

3V operation

V_{SS} = 0V

Parameter	Symbol	Condition	Rating	Unit
Supply voltage	V_{DD}		2.7 to 3.6	V
Input voltage	V_{IN}		V_{SS} to V_{DD}	V
Operating temperature	T_{OPR}		–40 to +85	°C
Operating frequency	f_{OSC}	$C_L \leq$ 15pF	4 to 60	MHz
		$C_L \leq$ 30pF	4 to 40	MHz

5V operation

V_{SS} = 0V

Parameter	Symbol	Condition	Rating	Unit
Supply voltage	V_{DD}		4.5 to 5.5	V
Input voltage	V_{IN}		V_{SS} to V_{DD}	V
Operating temperature	T_{OPR}		–40 to +85	°C
Operating frequency	f_{OSC}	$C_L \leq$ 30pF	4 to 60	MHz

Electrical Characteristics

3V operation

V_{DD} = 2.7 to 3.6V, V_{SS} = 0V, Ta = –40 to +85°C unless otherwise noted.

Parameter	Symbol	Condition		Rating min	Rating typ	Rating max	Unit
HIGH-level output voltage	V_{OH}	Q: Measurement cct 1, V_{DD} = 2.7V, I_{OH} = 4mA		2.1	2.4	–	V
LOW-level output voltage	V_{OL}	Q: Measurement cct 1, V_{DD} = 2.7V, I_{OL} = 4mA		–	0.3	0.4	V
HIGH-level input voltage	V_{IH}	INHN		0.7V_{DD}	–	–	V
LOW-level input voltage	V_{IL}	INHN		–	–	0.3V_{DD}	V
Output leakage current	I_Z	Q: Measurement cct 2, INHN = LOW	$V_{OH} = V_{DD}$	–	–	10	µA
			$V_{OL} = V_{SS}$	–	–	10	µA
Current consumption	I_{DD}	Measurement cct 3, load cct 1, INHN = open, C_L = 15pF, f = 60MHz	CF5014AL1	–	6.5	13	mA
			CF5014AL2	–	4	8	mA
			CF5014AL3	–	3	6	mA
			CF5014AL4	–	2.5	5	mA
			CF5014AL5	–	2	4	mA
Standby current	I_{ST}	Measurement cct 3, INHN = LOW		–	–	5	µA
INHN pull-up resistance	R_{UP1}	Measurement cct 4		2	6	18	MΩ
	R_{UP2}			30	100	300	kΩ
Feedback resistance	R_f	Measurement cct 5		100	300	600	kΩ
Built-in capacitance	C_G	Design value. A monitor pattern on a wafer is tested.		15.3	18	20.7	pF
	C_D			15.3	18	20.7	pF

5V operation

V_{DD} = 4.5 to 5.5V, V_{SS} = 0V, Ta = –40 to +85°C unless otherwise noted.

Parameter	Symbol	Condition		Rating min	Rating typ	Rating max	Unit
HIGH-level output voltage	V_{OH}	Q: Measurement cct 1, V_{DD} = 4.5V, I_{OH} = 8mA		3.9	4.2	–	V
LOW-level output voltage	V_{OL}	Q: Measurement cct 1, V_{DD} = 4.5V, I_{OL} = 8mA		–	0.3	0.4	V
HIGH-level input voltage	V_{IH}	INHN		0.7V_{DD}	–	–	V
LOW-level input voltage	V_{IL}	INHN		–	–	0.3V_{DD}	V
Output leakage current	I_Z	Q: Measurement cct 2, INHN = LOW	V_{OH} = V_{DD}	–	–	10	µA
			V_{OL} = V_{SS}	–	–	10	µA
Current consumption	I_{DD}	Measurement cct 3, load cct 1, INHN = open, C_L = 30pF, f = 60MHz	CF5014AL1	–	17	34	mA
			CF5014AL2	–	11.5	23	mA
			CF5014AL3	–	8.5	17	mA
			CF5014AL4	–	7	14	mA
			CF5014AL5	–	6	12	mA
Standby current	I_{ST}	Measurement cct 3, INHN = LOW		–	–	10	µA
INHN pull-up resistance	R_{UP1}	Measurement cct 4		1	3	9	MΩ
	R_{UP2}			10	50	150	kΩ
Feedback resistance	R_f	Measurement cct 5		100	300	600	kΩ
Built-in capacitance	C_G	Design value. A monitor pattern on a wafer is tested.		15.3	18	20.7	pF
	C_D			15.3	18	20.7	pF

Switching Characteristics

3V operation

V_{DD} = 2.7 to 3.6V, V_{SS} = 0V, Ta = –40 to +85°C unless otherwise noted.

Parameter	Symbol	Condition		Rating min	Rating typ	Rating max	Unit
Output rise time	t_{r1}	Measurement cct 3, load cct 1, 0.1V_{DD} to 0.9V_{DD}	C_L = 15pF	–	3	6	ns
	t_{r2}		C_L = 30pF	–	5	10	
Output fall time	t_{f1}	Measurement cct 3, load cct 1, 0.9V_{DD} to 0.1V_{DD}	C_L = 15pF	–	3	6	ns
	t_{f2}		C_L = 30pF	–	5	10	
Output duty cycle[1]	Duty1	Measurement cct 3, load cct 1, V_{DD} = 3.0V, Ta = 25°C	C_L = 15pF f = 60MHz	45	–	55	%
	Duty2		C_L = 30pF f = 40MHz	45	–	55	%
Output disable delay time[2]	t_{PLZ}	Measurement cct 6, load cct 1, V_{DD} = 3.0V, Ta = 25°C, C_L = 15pF		–	–	100	ns
Output enable delay time[2]	t_{PZL}			–	–	100	ns

1. The duty cycle characteristic is checked the sample chips of each production lot.
2. Oscillator stop function is built-in. When INHN goes LOW, normal output stops. When INHN goes HIGH, normal output is not resumed until after the oscillator start-up time has elapsed.

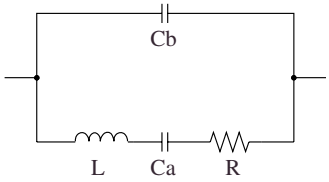
5V operation

V_{DD} = 4.5 to 5.5V, V_{SS} = 0V, Ta = –40 to +85°C unless otherwise noted.

Parameter	Symbol	Condition		Rating min	Rating typ	Rating max	Unit
Output rise time	t_{r1}	Measurement cct 3, load cct 1, 0.1V_{DD} to 0.9V_{DD}	C_L = 15pF	–	1.8	3.5	ns
	t_{r2}		C_L = 30pF	–	3	6	
Output fall time	t_{f1}	Measurement cct 3, load cct 1, 0.9V_{DD} to 0.1V_{DD}	C_L = 15pF	–	1.8	3.5	ns
	t_{f2}		C_L = 30pF	–	3	6	
Output duty cycle[1]	Duty1	Measurement cct 3, load cct 1, V_{DD} = 5.0V, Ta = 25°C	C_L = 30pF f = 60MHz	45	–	55	%
Output disable delay time[2]	t_{PLZ}	Measurement cct 6, load cct 1, V_{DD} = 5.0V, Ta = 25°C, C_L = 15pF		–	–	100	ns
Output enable delay time[2]	t_{PZL}			–	–	100	ns

1. The duty cycle characteristic is checked the sample chips of each production lot.
2. Oscillator stop function is built-in. When INHN goes LOW, normal output stops. When INHN goes HIGH, normal output is not resumed until after the oscillator start-up time has elapsed.

Current consumption and Output waveform with NPC's standard crystal



f [MHz]	R [Ω]	L [mH]	Ca [fF]	Cb [pF]
40	8.23	5.72	2.77	2.20
50	16.12	6.88	1.48	1.15
60*	–	–	–	–

* The 60MHz crystal data is confidential.

FUNCTIONAL DESCRIPTION

Standby Function

When INHN goes LOW, the oscillator stops and the oscillator output on Q becomes high impedance.

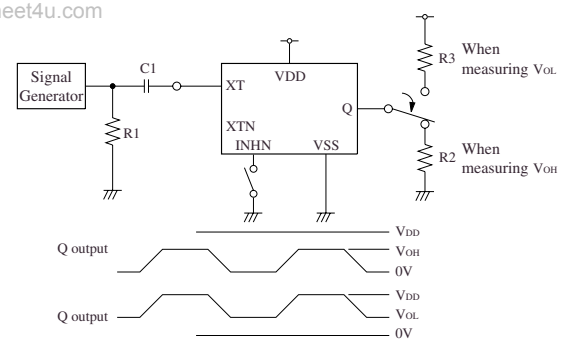
INHN	Q	Oscillator
HIGH (or open)	Any f_O, $f_O/2$, $f_O/4$, $f_O/8$ or $f_O/16$ output frequency	Normal operation
LOW	High impedance	Stopped

Power-save Pull-up Resistance

The INHN pull-up resistance changes in response to the input level (HIGH or LOW). When INHN goes LOW (standby state), the pull-up resistance becomes large to reduce the current consumption during standby.

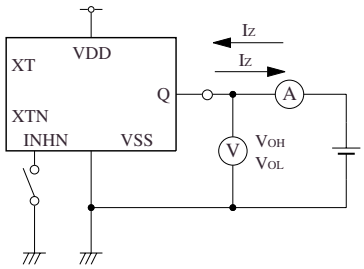
MEASUREMENT CIRCUITS

Measurement cct 1

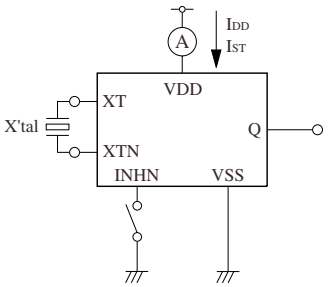


2Vp-p, 10MHz sine wave input signal
C1: 0.001µF
R1: 50Ω
R2: 525Ω (3V operation)
488Ω (5V operation)
R3: 575Ω (3V operation)
512Ω (5V operation)

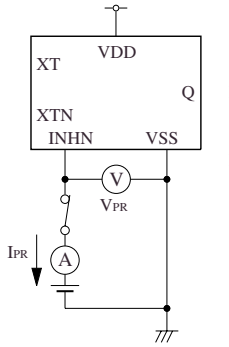
Measurement cct 2



Measurement cct 3



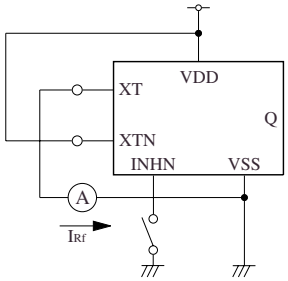
Measurement cct 4



$$R_{UP1} = \frac{V_{DD}}{I_{PR}} \quad (V_{PR} = V_{SS})$$

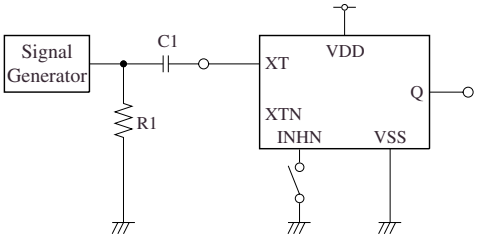
$$R_{UP2} = \frac{V_{DD} - V_{PR}}{I_{PR}} \quad (V_{PR} = 0.7V_{DD})$$

Measurement cct 5



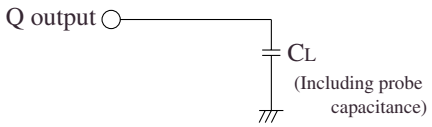
$$R_f = \frac{V_{DD}}{I_{Rf}}$$

Measurement cct 6



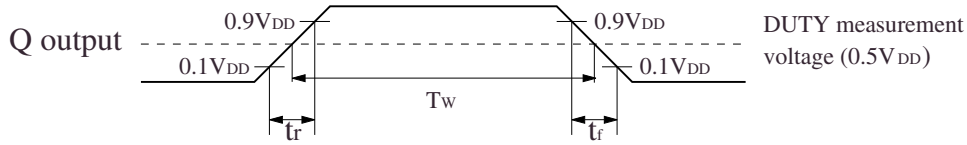
2Vp-p, 10MHz sine wave input signal
C1: 0.001µF
R1: 50Ω

Load cct 1

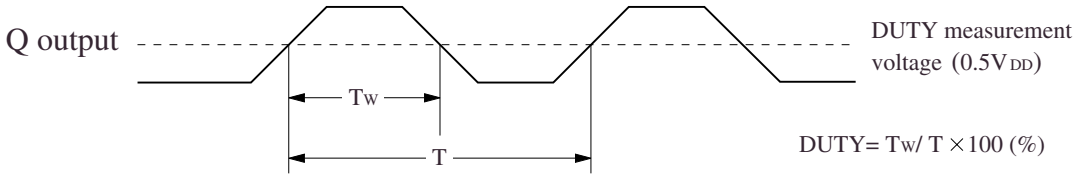


Switching Time Measurement Waveform

Output duty level

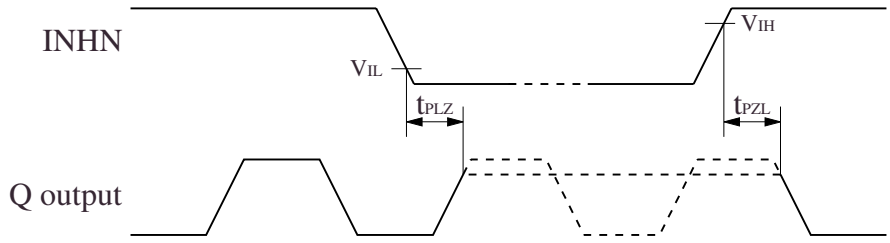


Output duty cycle



Output Enable/Disable Delay

when the device is in standby, the oscillator stops. When standby is released, the oscillator starts and stable oscillator output occurs after a short delay.



INHN input waveform tr = tf ≤ 10ns

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NC0205AE 2003.02